

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-THYRISTOR

TLP747JFOFFICE MACHINE
SWITCHING POWER SUPPLY

The TOSHIBA TLP747JF consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

All parameters are tested to the specification of TLP747J.
(both condition and limits)

- Peak Off-State Voltage : 600V (Min.)
- Trigger LED Current : 15mA (Max.)
- On-State Current : 150mA (Max.)
- UL Recognized : UL1577, File No.E67349
- BSI Approved : BS EN60065 : 1994,
Certificate No. 7364
BS EN60950 : 1992,
Certificate No. 7365
- SEMKO Approved : SS4330784, Certificate No. 9325163
No. 9522142
- Isolation Voltage : 4000Vrms (Min.)
- Option (D4) type
VDE Approved : DIN VDE0884 / 06.92,
Certificate No. 74286, 91808

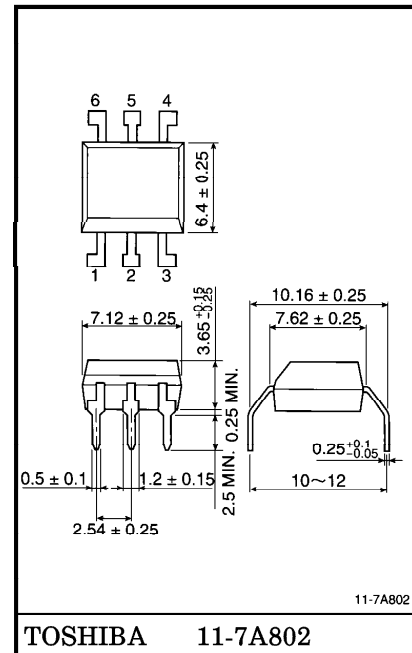
Maximum Operating Insulation Voltage : 890, 1130V_{PK}

Highest Permissible Over Voltage : 6000, 8000V_{PK}

(Note) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

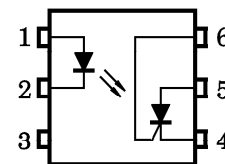
- Creepage Distance : 8.0mm (Min.)
- Clearance : 8.0mm (Min.)
- Internal Creepage Path : 4.0mm (Min.)
- Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
DIN 57 804.VDE0804 / 1.83
DIN IEC65 / VDE0860 / 8.81
DIN IEC380 / VDE0806 / 8.81
DIN IEC435 / VDE0805 / Draft Nov.84
DIN IEC601T1 / VDE0750T1 / 5.82
BS7002 : 1989 (EN60950)

Unit in mm



Weight : 0.42g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : CATHODE
- 5 : ANODE
- 6 : GATE

961001EBC2

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.